

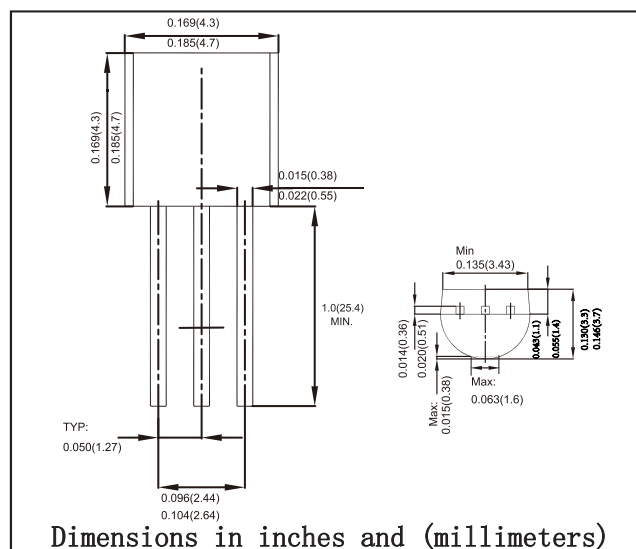
TO-92 Plastic-Encapsulate Transistors

FEATURES

- Collector Current: $I_C=0.1A$
- TRANSISTOR(NPN)
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MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.1	A
P_D	Collector Power Dissipation	450	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	277.7	°C /W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ#	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50V, I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=35V, I_B=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5V, I_C=1mA$	60		1000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=5mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=5mA$			1	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA$ $f=30MHz$	150			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	A	B	C	D
Range	60-150	100-300	200-600	400-1000

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

